



P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low R_{DS(ON)}:
 - $40 \text{ m}\Omega$ @V_{GS} = -4.5V
 - $70 \text{ m}\Omega$ @V_{GS} = -2.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

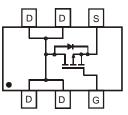
Mechanical Data

- Case: SOT26
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)





Top View



Top View Internal Schematic

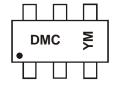
Ordering Information (Note 3)

Part Number	Case	Packaging
DMP2066LDM-7	SOT26	3000/Tape & Reel
DMP2066LDMQ-7	SOT26	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



DMC = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012	!	2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	2	1	5	6	7	0	0	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 4) Continuous	T _A = 25°C T _A = 70°C	I _D	-4.6 -3.7	А
Pulsed Drain Current (Note 5)		I _{DM}	-18	А
Body-Diode Continuous Current (Note 4)		Is	2.0	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 4)	P_{D}	1.25	W
Thermal Resistance, Junction to Ambient (Note 4); Steady-State	$R_{ hetaJA}$	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

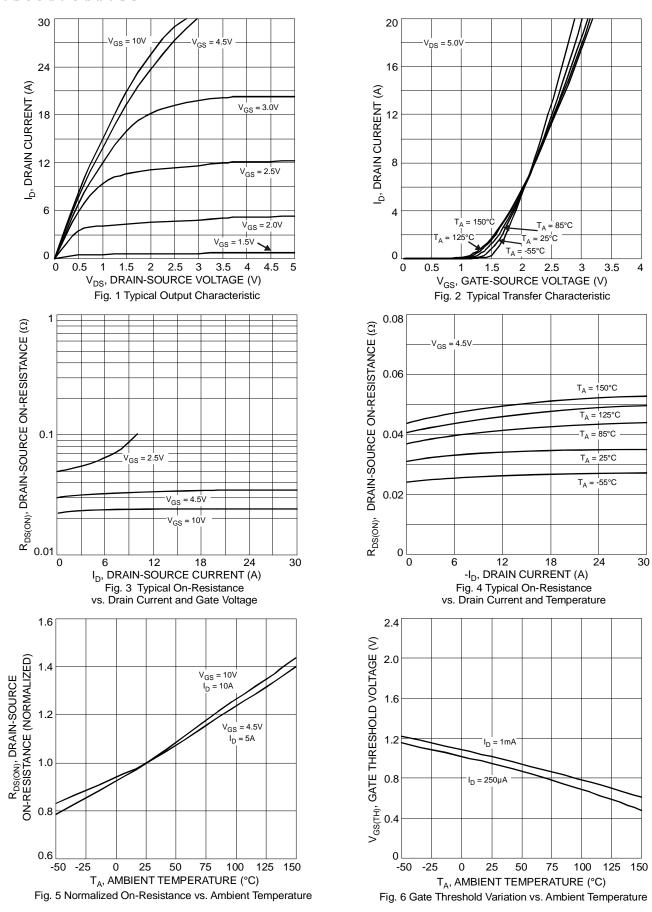
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC PARAMETERS							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current T _J = 25°C	IDSS	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Body Leakage Current	I _{GSS}	_		±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$	
Gate Threshold Voltage	V _{GS(th)}	-0.6	-0.96	-1.2	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
On State Drain Current (Note 6)	I _{D (ON)}	-15		_	Α	$V_{GS} = -4.5V, V_{DS} = -5V$	
Static Drain-Source On-Resistance (Note 6)	R _{DS (ON)}		29	40	mΩ	$V_{GS} = -4.5V$, $I_D = -4.6A$	
,	TVDS (ON)		55	70		$V_{GS} = -2.5V, I_D = -3.8A$	
Forward Transconductance (Note 6)	g _{FS}		9	_	S	$V_{DS} = -10V, I_{D} = -4.6A$	
Diode Forward Voltage (Note 6)		-0.5	-0.72	-1.4	V	$I_S = -2.1A$, $V_{GS} = 0V$	
Maximum Body-Diode Continuous Current (Note 4)	Is	_	_	1.7	Α	_	
DYNAMIC PARAMETERS (Note 7)							
Input Capacitance	C _{iss}	_	820	_	pF	4577.77	
Output Capacitance	Coss	_	200		pF	$V_{DS} = -15V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	160		pF	1 = 1.0101112	
Gate Resistance	R _G	_	2.5		Ω	$V_{DS} = 0V, V_{GS} = 0V$ f = 1.0MHz	
SWITCHING CHARACTERISTICS							
Total Gate Charge	Q_G	_	10.1	_	nC	$V_{DS} = -10V, V_{GS} = -4.5V,$ $I_{D} = -4.5A$	
Gate-Source Charge	Q_{GS}	_	1.5	_			
Gate-Drain Charge	Q_{GD}	_	4.3	_		ID = -4.5A	
Turn-On Delay Time	t _{d(on)}	_	4.4	_			
Rise Time	t _r	_	9.9	_		$V_{DS} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{d(off)}	_	28.0	_	ns	$I_D = -1A, R_G = 6.0\Omega$	
Fall Time	t _f		23.4				

Notes:

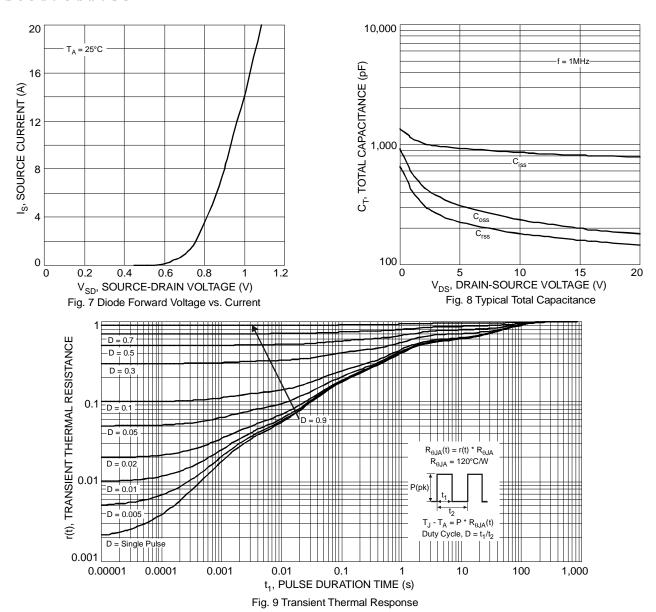
- 4. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t \leq 10s. 5. Repetitive Rating, pulse width limited by junction temperature. 6. Test pulse width t = 300 μ s.

- 7. Guaranteed by design. Not subject to production testing.

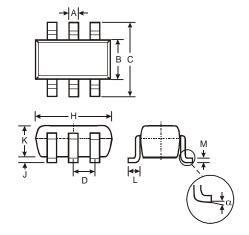








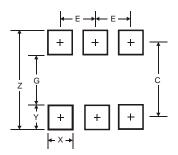
Package Outline Dimensions



SOT26							
Dim	Min	Max	Тур				
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_		0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
K	1.00	1.30	1.10				
L	0.35	0.55	0.40				
М	0.10	0.20	0.15				
α	0°	8°	_				
AII D	All Dimensions in mm						



Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
С	2.40
E	0.95

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